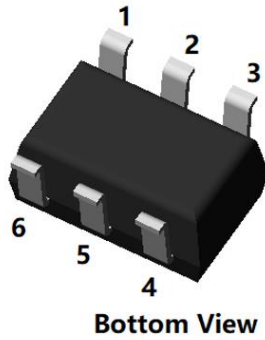
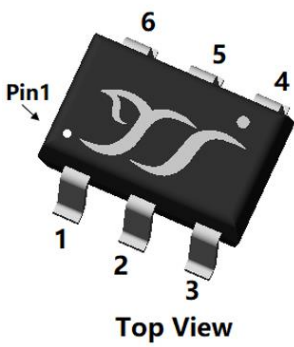
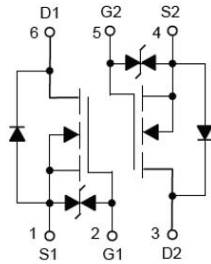


## N-Channel Enhancement Mode Field Effect Transistor



**SOT-363**



### Product Summary

- $V_{DS}$  20 V
- $I_D$  0.8 A
- $R_{DS(ON)}$  ( at  $V_{GS}=4.5V$ ) <300 mohm
- $R_{DS(ON)}$  ( at  $V_{GS}=2.5V$ ) <400 mohm
- $R_{DS(ON)}$  ( at  $V_{GS}=1.8V$ ) <700 mohm
- ESD Protected Up to 2.0KV (HBM)

### General Description

- Trench Power LV MOSFET technology
- High Power and current handing capability
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

### Applications

- PWM application
- Load switch

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	$V_{DS}$	20	V
Gate-source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current	$I_D$	$T_A=25^\circ C$ @ Steady State	0.8
		$T_A=70^\circ C$ @ Steady State	0.6
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	3.3	A
Total Power Dissipation @ $T_A=25^\circ C$	$P_D$	0.29	W
Thermal Resistance Junction-to-Ambient @ Steady State	$R_{\theta JA}$	420	$^\circ C/W$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ C$

### ■ Ordering Information

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL3134KADW	F2	34KA	3000	30000	120000	7" reel



# YJL3134KADW

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±10V, V <sub>DS</sub> =0V		2.5	±10	μA
		V <sub>GS</sub> = ±8V, V <sub>DS</sub> =0V		500	±2000	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	0.35	0.75	1.1	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> =0.5A		220	300	mΩ
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> =0.45A		290	400	
		V <sub>GS</sub> = 1.8V, I <sub>D</sub> =0.2A		420	700	
Diode Forward Voltage <sup>C</sup>	V <sub>SD</sub>	I <sub>S</sub> =0.5A, V <sub>GS</sub> =0V		0.85	1.2	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				0.5	A
Gate Resistance	R <sub>g</sub>	f=1 MHz		50		Ω
<b>Dynamic Parameters<sup>B</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHZ		33		pF
Output Capacitance	C <sub>oss</sub>			20		
Reverse Transfer Capacitance	C <sub>rss</sub>			10		
<b>Switching Parameters<sup>B</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =10V, I <sub>D</sub> =0.5A		0.8		nC
Gate Source Charge	Q <sub>gs</sub>			0.3		
Gate Drain Charge	Q <sub>gd</sub>			0.15		
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =0.5A, di/dt=20A/us		0.4		ns
Reverse Recovery Time	t <sub>rr</sub>			14.4		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =4.5V, V <sub>DD</sub> =10V, R <sub>G</sub> =10Ω, I <sub>D</sub> =500mA		4		ns
Turn-on Rise Time	t <sub>r</sub>			18.8		
Turn-off Delay Time	t <sub>D(off)</sub>			10		
Turn-off Fall Time	t <sub>f</sub>			23		

A. Repetitive Rating: Pulse width limited by maximum junction temperature.

B. These parameters have no way to verify.

C. Pulse Test: Pulse Width≤300us, Duty Cycle≤0.5%.



## ■ Typical Performance Characteristics

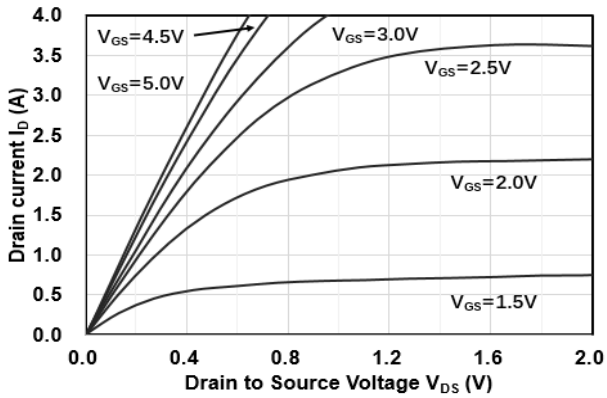


Figure1. Output Characteristics

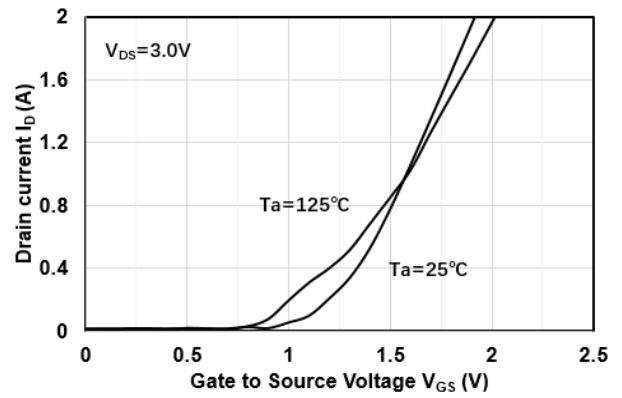


Figure2. Transfer Characteristics

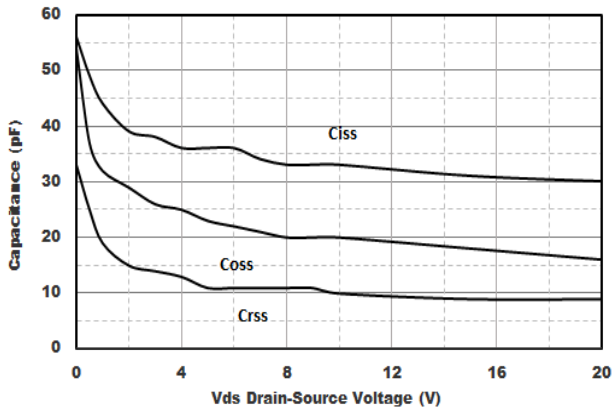


Figure3. Capacitance Characteristics

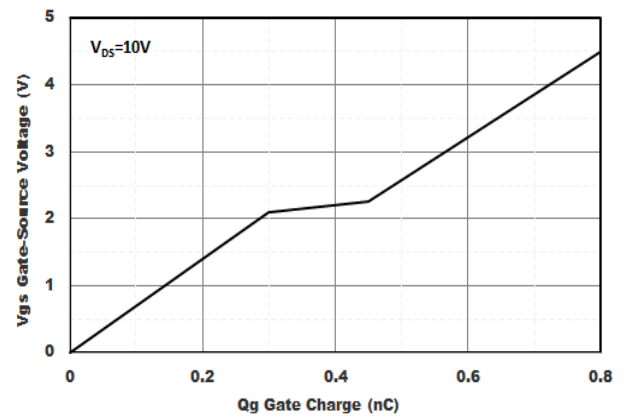


Figure4. Gate Charge

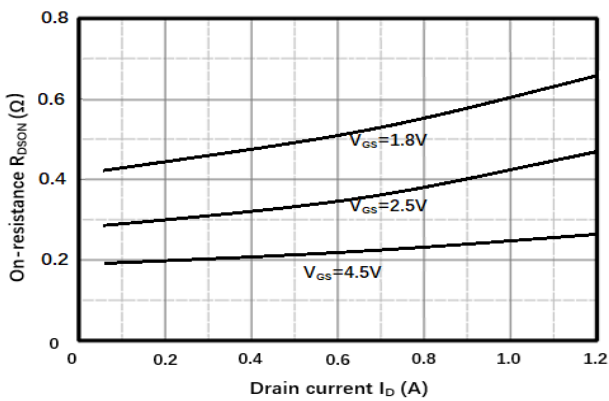


Figure5. Drain-Source on Resistance

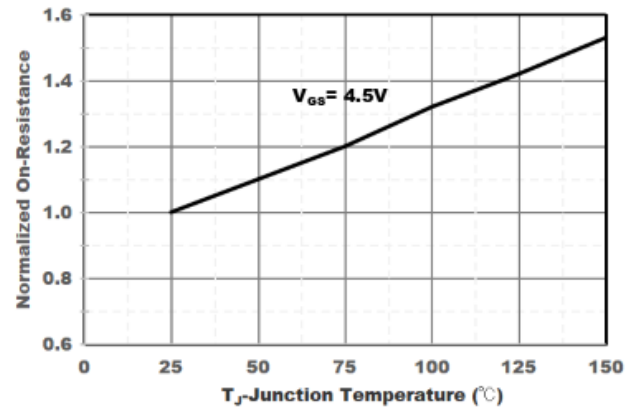


Figure6. Drain-Source on Resistance



# YJL3134KADW

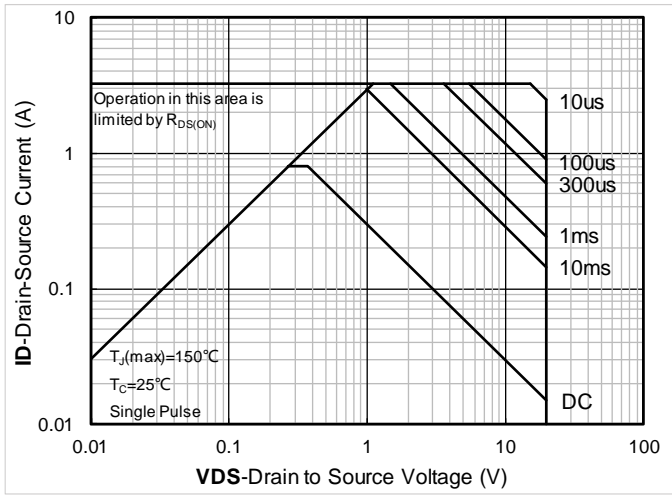


Figure7. Safe Operation Area

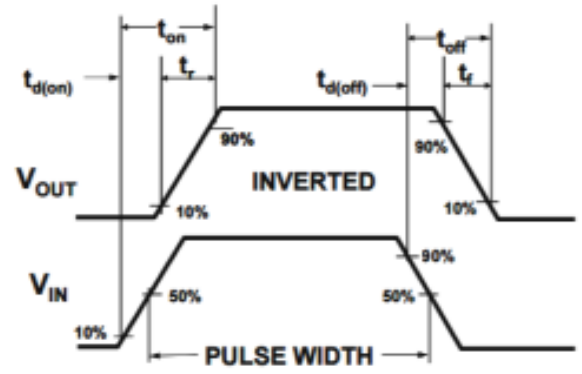
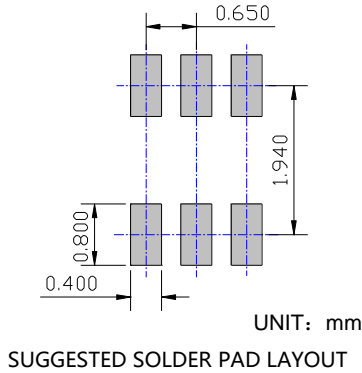
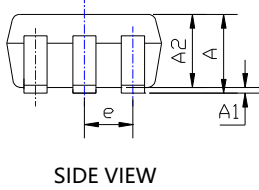
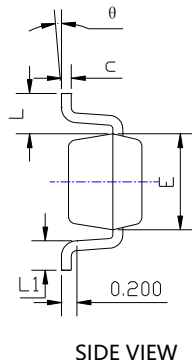
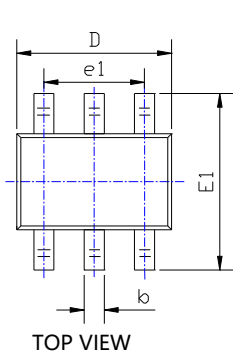


Figure8. Switching wave



# YJL3134KADW

## ■SOT-363 Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.035	0.043	0.900	1.100
A1	0.000	0.004	0.000	0.100
A2	0.035	0.039	0.900	1.000
b	0.006	0.014	0.150	0.350
c	0.004	0.010	0.100	0.250
D	0.071	0.087	1.800	2.200
E	0.045	0.053	1.150	1.350
E1	0.085	0.096	2.150	2.450
e	0.026TYP		0.650TYP	
e1	0.047	0.055	1.200	1.400
L	0.021REF		0.525REF	
L1	0.010	0.018	0.260	0.460
θ	0°	8°	0°	8°

- NOTE:
- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
  - 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
  - 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



## Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website [http:// www.21yangjie.com](http://www.21yangjie.com) , or consult your nearest Yangjie's sales office for further assistance.